

ON THE FORMATION OF VACANCY
MICRODEFECTS IN DISLOCATION-FREE
SILICON SINGLE CRYSTALS

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S u m m a r y

We have experimentally shown that the vacancy grown-in microdefects of the *D*- and *B*-types are formed in the interstitial mode of the growth of dislocation-free silicon monocrystals. It is determined that the concentration of vacancy *D*- and *B*-microdefects is by two orders less than that of interstitial *D*- and *B*-microdefects.